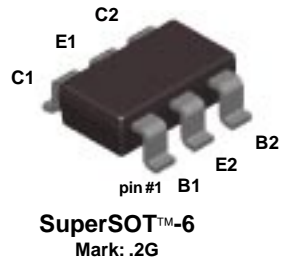


## FMBA56



### PNP Multi-Chip General Purpose Amplifier

This device is designed for general purpose amplifier applications at collector currents to 300 mA. Sourced from Process 73.

#### Absolute Maximum Ratings\* T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CES</sub>	Collector-Emitter Voltage	80	V
V <sub>CBO</sub>	Collector-Base Voltage	80	V
V <sub>EBO</sub>	Emitter-Base Voltage	4.0	V
I <sub>C</sub>	Collector Current - Continuous	500	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

**NOTES:**

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

#### Thermal Characteristics T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		FMBA56	
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	700	mW
		5.6	mW/°C
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	180	°C/W

# PNP Multi-Chip General Purpose Amplifier

(continued)

FMBA56

## Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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### OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	80			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 100 \mu\text{A}, I_E = 0$	80			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 100 \mu\text{A}, I_C = 0$	4.0			V
$I_{CEO}$	Collector-Cutoff Current	$V_{CE} = 60 \text{ V}, I_B = 0$			0.1	$\mu\text{A}$
$I_{CBO}$	Collector-Cutoff Current	$V_{CB} = 80 \text{ V}, I_E = 0$			0.1	$\mu\text{A}$

### ON CHARACTERISTICS

$h_{FE}$	DC Current Gain	$I_C = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 100 \text{ mA}, V_{CE} = 1.0 \text{ V}$	100			
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$			0.25	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = 100 \text{ mA}, V_{CE} = 1.0 \text{ V}$			1.2	V

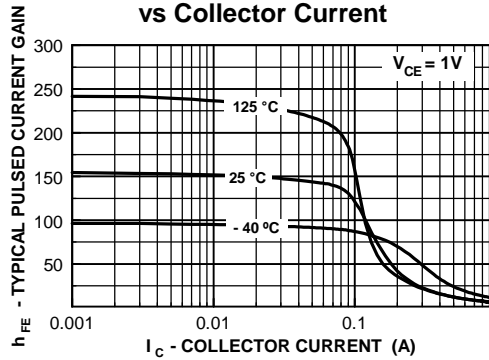
### SMALL SIGNAL CHARACTERISTICS

$f_T$	Current Gain - Bandwidth Product	$I_C = 100 \text{ mA}, V_{CE} = 1.0 \text{ V},$ $f = 100 \text{ MHz}$		125		MHz
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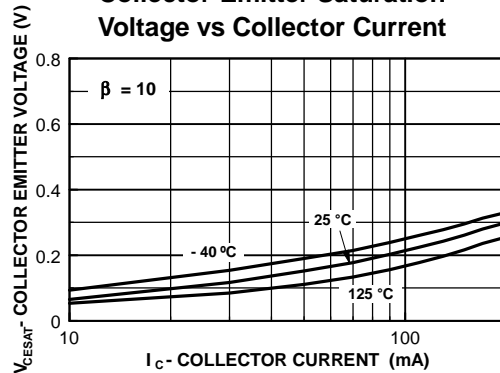
\*Pulse Test: Pulse Width  $\leq 300 \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

## Typical Characteristics

**Typical Pulsed Current Gain vs Collector Current**

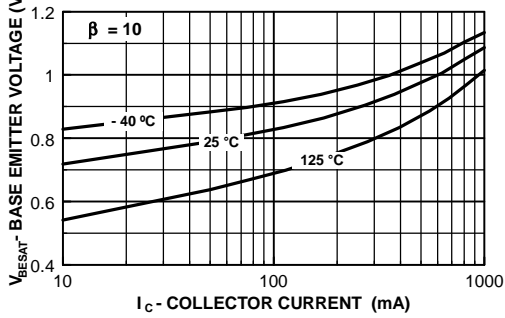


**Collector-Emitter Saturation Voltage vs Collector Current**

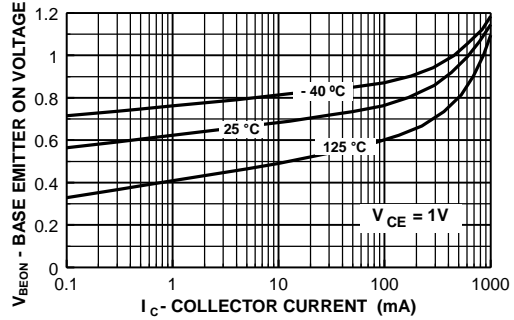


Typical Characteristics (continued)

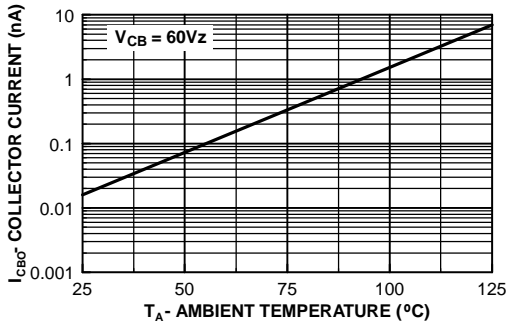
Base-Emitter Saturation Voltage vs Collector Current



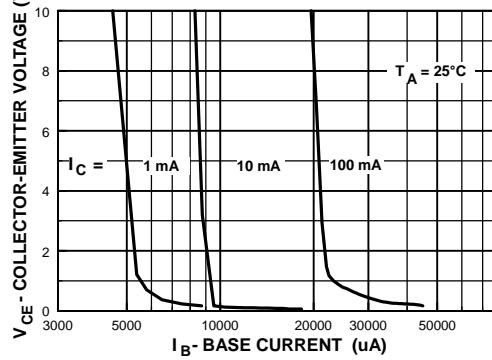
Base Emitter ON Voltage vs Collector Current



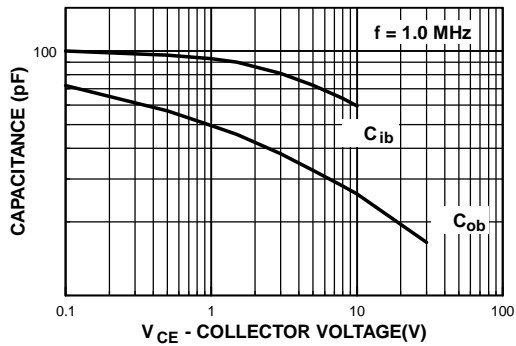
Collector-Cutoff Current vs. Ambient Temperature



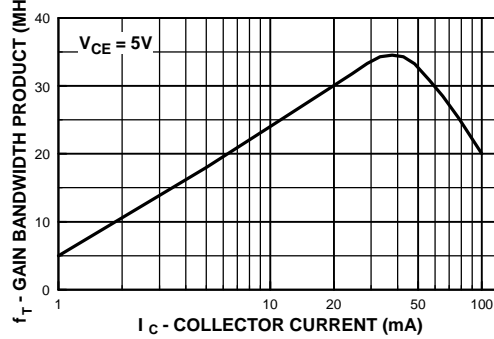
Collector Saturation Region



Input and Output Capacitance vs Reverse Voltage



Gain Bandwidth Product vs Collector Current



Typical Characteristics (continued)

